

## Features and Benefits

- Operating voltage range from 2.2V to 18V
- Very high magnetic sensitivity
- CMOS technology
- Chopper-stabilized amplifier stage
- Low current consumption
- Open drain output
- SOT23 3L and flat TO-92 3L  
both RoHS Compliant packages

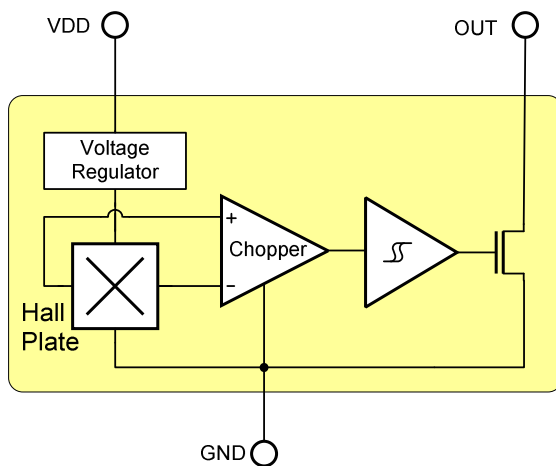
## Application Examples

- Automotive, Consumer and Industrial
- Solid-state switch
- Brushless DC motor commutation
- Speed detection
- Linear position detection
- Angular position detection
- Proximity detection

## Ordering Information

Part No.	Temperature Code	Package Code
US4881	E (-40 °C to 85 °C)	SO (SOT23-3L)
US4881	E (-40 °C to 85 °C)	UA (TO-92)
US4881	K (-40 °C to 125 °C)	SO (SOT23-3L)
US4881	K (-40 °C to 125 °C)	UA (TO-92)
US4881	L (-40 °C to 150 °C)	SO (SOT23-3L)
US4881	L (-40 °C to 150 °C)	UA (TO-92)

## 1 Functional Diagram



## 2 General Description

The Melexis US4881 is a bipolar Hall-effect switch designed in mixed signal CMOS technology.

The device integrates a voltage regulator, Hall sensor with dynamic offset cancellation system, Schmitt trigger and an open-drain output driver, all in a single package.

The low operating voltage and extended choice of temperature range make it suitable for use in automotive, industrial and consumer low voltage applications.

The devices are delivered in a Small Outline Transistor (SOT23) for surface mount process and in a Plastic Single In Line (TO-92 flat) for through-hole mount.

Both 3-lead packages are RoHS compliant.

**Table of Contents**

<b>1 Functional Diagram .....</b>	<b>1</b>
<b>2 General Description.....</b>	<b>1</b>
<b>3 Glossary of Terms .....</b>	<b>3</b>
<b>4 Absolute Maximum Ratings.....</b>	<b>3</b>
<b>5 Pin Definitions and Descriptions.....</b>	<b>3</b>
<b>6 General Electrical Specifications .....</b>	<b>4</b>
<b>7 Magnetic Specifications .....</b>	<b>4</b>
<b>8 Output Behaviour versus Magnetic Pole .....</b>	<b>4</b>
<b>9 Detailed General Description.....</b>	<b>5</b>
<b>10 Unique Features.....</b>	<b>5</b>
<b>11 Performance Graphs .....</b>	<b>6</b>
<b>12 Application Information.....</b>	<b>7</b>
12.1 Typical Three-Wire Application Circuit .....	7
12.2 Two-Wire Circuit .....	7
12.3 Automotive and Harsh, Noisy Environments Three-Wire Circuit .....	7
<b>13 Application Comments.....</b>	<b>7</b>
<b>14 Standard information regarding manufacturability of Melexis products with different soldering processes.....</b>	<b>8</b>
<b>15 ESD Precautions.....</b>	<b>8</b>
<b>16 Package Information.....</b>	<b>9</b>
16.1 SO Package (SOT23-3L).....	9
16.2 UA Package (TO-92 flat) .....	10
<b>17 Disclaimer.....</b>	<b>11</b>

### 3 Glossary of Terms

MilliTesla (mT), Gauss	Units of magnetic flux density: 1mT = 10 Gauss
RoHS	Restriction of Hazardous Substances
TSOT	Thin Small Outline Transistor (TSOT package) – also referred with the Melexis package code “SE”
ESD	Electro-Static Discharge
BLDC	Brush-Less Direct-Current

### 4 Absolute Maximum Ratings

Parameter	Symbol	Value	Units
Supply Voltage	V <sub>DD</sub>	20	V
Supply Current	I <sub>DD</sub>	50	mA
Output Voltage	V <sub>OUT</sub>	20	V
Output Current	I <sub>OUT</sub>	50	mA
Storage Temperature Range	T <sub>S</sub>	-50 to 150	°C
Maximum Junction Temperature	T <sub>J</sub>	165	°C
ESD Sensitivity (AEC Q100 002)	-	2.5	kV

Table 1: Absolute maximum ratings

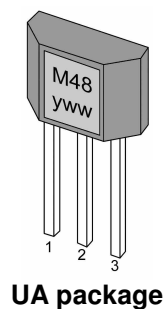
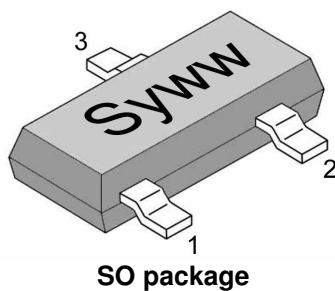
Exceeding the absolute maximum ratings may cause permanent damage. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Operating Temperature Range	Symbol	Value	Units
Temperature Suffix “E”	T <sub>A</sub>	-40 to 85	°C
Temperature Suffix “K”	T <sub>A</sub>	-40 to 125	°C
Temperature Suffix “L”	T <sub>A</sub>	-40 to 150	°C

### 5 Pin Definitions and Descriptions

SE Pin №	UA Pin №	Name	Type	Function
1	1	VDD	Supply	Supply Voltage pin
2	3	OUT	Output	Open Drain Output pin
3	2	GND	Ground	Ground pin

Table 2: Pin definitions and descriptions



## 6 General Electrical Specifications

DC Operating Parameters  $T_A = 25^\circ\text{C}$ ,  $V_{DD} = 12\text{V}$  (unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Supply Voltage	$V_{DD}$	Operating	2.2		18	V
Supply Current	$I_{DD}$	$B < B_{RP}$	1.5		5	mA
Output Saturation Voltage	$V_{DSon}$	$I_{OUT} = 20\text{mA}$ , $B > B_{OP}$			0.5	V
Output Leakage Current	$I_{OFF}$	$B < B_{RP}$ , $V_{OUT} = 24\text{V}$		0.01	10	$\mu\text{A}$
Output Rise Time	$t_r$	$R_L = 1\text{k}\Omega$ , $C_L = 20\text{pF}$		0.25		$\mu\text{s}$
Output Fall Time	$t_f$	$R_L = 1\text{k}\Omega$ , $C_L = 20\text{pF}$		0.25		$\mu\text{s}$
Maximum Switching Frequency	$F_{SW}$			10		KHz
SO Package Thermal Resistance	$R_{TH}$			350		$^\circ\text{C/W}$
UA Package Thermal Resistance	$R_{TH}$			200		$^\circ\text{C/W}$

Table 3: Electrical specifications

## 7 Magnetic Specifications

DC Operating Parameters  $T_A = 25^\circ\text{C}$ ,  $V_{DD} = 12\text{V}$  (unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Operating Point	$B_{OP}$		-1		6	mT
Release Point	$B_{RP}$		-6		1	mT
Hysteresis	$B_{HYST}$		2		6	mT

Table 4: Magnetic specifications

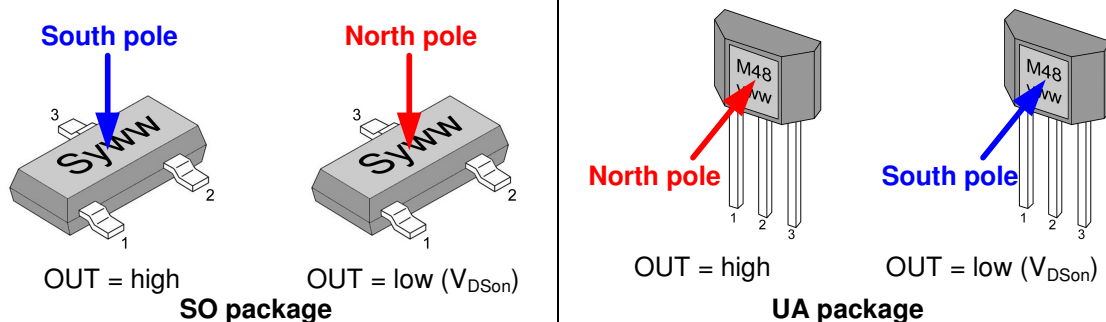
Note 1: For typical values, please refer to the performance graphs in section 11

## 8 Output Behaviour versus Magnetic Pole

DC Operating Parameters  $T_A = -40^\circ\text{C}$  to  $150^\circ\text{C}$ ,  $V_{DD} = 2.2\text{V}$  to  $18\text{V}$  (unless otherwise specified)

Parameter	Test Conditions (SO)	OUT (SO)	Test Conditions (UA)	OUT (UA)
South pole	$B < B_{RP}$	High	$B > B_{OP}$	Low
North pole	$B > B_{OP}$	Low	$B < B_{RP}$	High

Table 5: Output behaviour versus magnetic pole



## 9 Detailed General Description

Based on mixed signal CMOS technology, Melexis US4881 is a Hall-effect device with very high magnetic sensitivity. It allows using generic magnets, weak magnets or larger air gap.

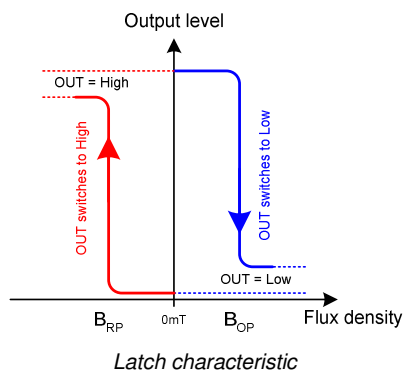
The chopper-stabilized amplifier uses switched capacitor techniques to suppress the offset generally observed with Hall sensors and amplifiers. The CMOS technology makes this advanced technique possible and contributes to smaller chip size and lower current consumption than bipolar technology. The small chip size is also an important factor to minimize the effect of physical stress. This combination results in more stable magnetic characteristics and enables faster and more precise design.

The operating voltage from 2.2V to 18V, low current consumption and large choice of operating temperature range according to "L", "K" and "E" specification make this device suitable for automotive, industrial and consumer low voltage applications.

The output signal is open-drain type. Such output allows simple connectivity with TTL or CMOS logic by using a pull-up resistor tied between a pull-up voltage and the device output.

## 10 Unique Features

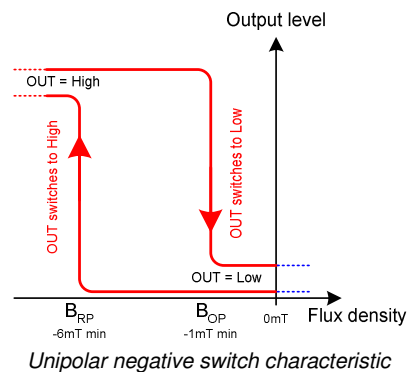
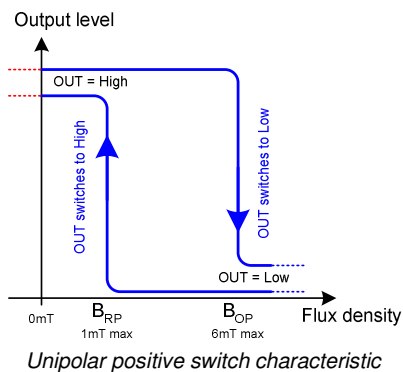
The US4881 exhibits bipolar magnetic switching characteristics. Therefore, it operates with both south and north poles.



Typically, the device behaves as a latch with symmetric operating and release switching points ( $B_{OP} = |B_{RP}|$ ). This means magnetic fields with equivalent strength and opposite direction drive the output high and low.

Removing the magnetic field ( $B \rightarrow 0$ ) keeps the output in its previous state. This latching property defines the device as a magnetic memory.

Depending on the magnetic switching points, the device may also behave as a unipolar positive switch ( $B_{OP}$  and  $B_{RP}$  strictly positive) or negative switch ( $B_{OP}$  and  $B_{RP}$  strictly negative). That is the output can be set high and low by only using one magnetic pole. In such case, removing the magnetic field changes the output level.



In latch, positive or negative switch behaviour, a magnetic hysteresis  $B_{HYST}$  keeps  $B_{OP}$  and  $B_{RP}$  separated by a minimal value. This hysteresis prevents output oscillation near the switching point.